



Secondary Side Synchronous Rectifier (SR)

FEATURES

- Secondary Side Synchronous Rectifier(SR) for Flyback converters
- Supports High-Side and Low-Side in DCM and Quasi-Resonant Topologies
- <300uA Low Quiescent Current
- Built-in HV Supplies without Aux-Winding for VDD supply
- Integrated with 45V Power MOSFET
- Built-in Protections:
 - VDD UVLO
 - VDD Clamper by >5mA sink current
- Available with SOP-8 Package

APPLICATIONS

- Flyback converters
- Chargers

TYPICAL APPLICATION CIRCUIT

GENERAL DESCRIPTION

KP411X is a family of secondary side synchronous rectifier, that replaced Schottky diodes by combined with an ultra low on-state resistance power MOSFET for high-efficiency flyback converters. It supports High-Side and Low-Side in DCM and Quasi-Resonant Topologies.

KP411X is built-in HV supplies for VDD capacitor, that can eliminate the aux-winding of VDD supply for cost saving.

KP411X integrates protections of Under Voltage Lockout (UVLO), VDD Clamper.





Pin Configuration





Ordering Information





KP4110/KP4111

Secondary Side Synchronous Rectifier

Absolute Maximum Ratings (Note 1)

Parameter	Value	Unit
Drain Pin Voltage Range	-0.3 to 45	V
VDD DC Supply Voltage	7.4	V
VDD DC Clamp Current	5	mA
Package Thermal ResistanceJunction to Ambient (SOP-8)	165	°C/W
Maximum Junction Temperature	150	°C
Storage Temperature Range	-65 to 150	°C
Lead Temperature (Soldering, 10sec.)	260	°C
ESD Capability, HBM (Human Body Model)	3	kV
ESD Capability, MM (Machine Model)	250	V

Recommended Operation Conditions (Note 2)

Parameter	Value	Unit
Operating Ambient Temperature	-40 to 125	°C

Electrical Characteristics (Ta = 25°C, if not otherwise noted)

	Symbol	Parameter	Test Conditions	Min	Тур.	Max	Unit		
	Supply Voltage Section(VDD Pin)								
I _Q		Quiescent Operation Current	nt VDD=6V,Drain=0V		150	200	uA		
	V _{DD_reg}	HV supply VDD regulation Voltage	Drain=12V	6.7	7.1	7.5	V		
	I _{HV}	HV supply current	Drain=12V,VDD=5.5V	15		30	mA		
	V_{DD_ON}	VDD Start-up Voltage	VDD rising	3.7	4	4.3	V		
	V_{DD_OFF}	VDD Under Voltage Lockout Enter	VDD falling	2.8	3.1	3.4	V		
	$V_{\text{DD}_\text{Clamp}}$	VDD Zener Clamp Voltage	I(V _{DD}) = 5mA		7.4		V		



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Secondary Side Synchronous Rectifier

Internal MOSFET and Control Section(Drain Pin)						
Vth_off	Internal synchronous MOSFET turn off threshold voltage		-15	-10	-5	mV
Vth_on	Iternnal synchronous MOSFET turn on threshold voltage			-300		mV
Rds_on	Internal synchronous MOSFET on-state resistance	KP4110		15	20	mΩ
Rus_011		KP4111		10	15	mΩ
Td_on	Internal synchronous MOSFET turn on delay time				200	ns
Td_off	Internal synchronous MOSFET turn off delay time				60	ns
V_{BR}	Internal synchronous MOSFET Drain Source Breakdown Voltage		45			V

Note 1. Stresses listed as the above "Maximum Ratings" may cause permanent damage to the device. These are for stress ratings. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to maximum rating conditions for extended periods may remain possibility to affect device reliability.

.ide it Note 2. The device is not guaranteed to function outside its operating conditions.



Characterization Plots





Operation Description

KP411X is a family of secondary side synchronous rectifier, that replaced Schottky diodes by combined with an ultra low on-state resistance power MOSFET for high-efficiency flyback converters. It supports High-Side and Low-Side in DCM and Quasi-Resonant Topologies. KP411X is built-in HV supplies for VDD capacitor, that can eliminate the aux-winding of VDD supply for cost saving

• 7.1V Regulator

In KP411X, the 7.1V regulator charges VDD holdup capacitor to 7.1V by drawing a current from the Drain pin during the on state of primary side. A capacitor value about 1uF is sufficient for both high frequency decoupling and energy storage.

• System Start-Up Operation

After system power up, VDD hold up capacitor is charged by the internal LDO through Drain pin.

When VDD pin voltage is below UVLO threshold (3.1V typically), the IC is in sleep mode and the internal synchronous MOSFET is keeping off. The current flows through body diode of the internal synchronous MOSFET. When VDD pin voltage reaches the turn on threshold (4V typically), the IC begins working. The internal synchronous MOSFET can be only turned on during the demagnetization time of the transformer.

• Turn-on Phase

When the internal synchronous MOSFET is off, current will flow through its body diode which can generate a negative Vds(<-500mV) across it. The body diode drop voltage Vds is much smaller than the turn on threshold of KP411X (-300mV typically), which will turn on the internal synchronous MOSFET after about 200ns turn on delay (Td_on). (Shown in Fig 1)

• Turn-off Phase



During the turn-on period of the internal synchronous MOSFET, The KP411X senses the drop voltage Vds across the on-state resistance of the MOSFET. When Vds is higher than the turn off threshold (-10mV typically), the internal synchronous MOSFET will be turned off after about 60ns turn on delay (Td_off). (Shown in Fig 1)



Fig 1

• Leading Edge Blanking (LEB)

Each time the internal synchronous MOSFET is switched on, a turn-on spike occurs across the Drain and GND. To avoid premature termination of the switching pulse, an internal leading edge blanking circuit is built in. During this blanking period (1us typically), the turn-off comparator is disabled and cannot switch off the internal synchronous MOSFET.



Package Dimension



	Dimensions in Millimeters		Dimensions in Inches		
Symbol	Min	Max	Min	Max	
А	1.350	1.750	0.053	0.069	
A1 🔺	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
C	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270	(BSC)	0.050 (BSC)		
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



Revision History

DATE	REV.	DESCRIPTI	ON
2017/07/10	1.0	First Relea	se
2017/08/09	1.01	Modify "Absolute Maximum Ratings" and	"Electrical Characteristics" table
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